

論文 / 著書情報
Article / Book Information

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Title(English)	Interface Structure and Magnetic Properties of BiFeO ₃ -based Layered Films
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種別(和文)	論文要旨
Type(English)	Summary

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論文要旨

THESIS SUMMARY

専攻 : Department of	材料物理学	専攻	申請学位 (専攻分野) : Academic Degree Requested	博士 (工学)	Doctor of
学生氏名 : Student's Name	王 月		指導教員 (主) : Academic Supervisor(main)	史 蹟	
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要旨 (英文 800 語程度)

Thesis Summary (approx.800 English Words)

Interface structure and magnetic properties of BiFeO₃-based layered films have been investigated. BiFeO₃ is the only room temperature single-phase multiferroic material discovered at present and has a promising application in new generation devices. Chapter 1 describes background information and current research situation of BiFeO₃. Chapter 2 and 3 focus on the structure characterization of BiFeO₃ films prepared on various substrate (amorphous SiO₂, single crystal MgO and SrTiO₃ substrates) and conductive under layer (TiN film). Chapter 4 and 5 report interface induced magnetic properties of BiFeO₃/L₁₀ ordered Co_{0.5}Pt_{0.5} and Co₂FeSi/BiFeO₃ layered films, respectively. Chapter 6 is the final conclusion of this thesis.

In chapter 2, BiFeO₃ films are prepared on three typical substrates by sputtering method. No pure crystal BiFeO₃ phase can be obtained on amorphous SiO₂ substrates, while crystal BiFeO₃ films are grown on single crystal substrates. On MgO substrates, which provides a large tensile strain (~ 6.6 %), BiFeO₃ shows three growth orientations: (001), (110) and (111). And BiFeO₃ film displays epitaxial growth on SrTiO₃ substrates, which imposes a relatively small compressive strain (~ - 1.4 %). Such differences indicates BiFeO₃ film growth is quite sensitive to substrates.

Chapter 3 explores BiFeO₃ film growth on TiN under layers. Three substrates are used: amorphous SiO₂, MgO (001) and MgO (111) substrates. TiN under layers show (111) orientation on amorphous SiO₂ and MgO (111) substrates, and no crystalline BiFeO₃ phase can be induced on (111)-textured TiN under layers. On the other hand, (001) TiN film is grown on MgO (001) substrates and crystalline BiFeO₃ films are obtained on (001) TiN under layers. This can be understood from stability difference between (001) and (111) surface. Compared to (001), (111) surface of BiFeO₃ are energetically unfavourable, and (111) TiN cannot trigger the nucleation of BiFeO₃ phase. Besides, epitaxial BiFeO₃ growth can be prepared on TiN (001) under layers at reduced deposition temperature of 500 °C. At this condition, two kinds of structure co-exist: tetragonal (T) and rhombohedral (R). The crystallographic relationship can be expressed as: T-BiFeO₃ (001)[100]//TiN (001)[100] and R-BiFeO₃ (001)[100]//TiN (001)[100].

Magnetic properties in perpendicular direction of BiFeO₃/L₁₀ ordered CoPt films are reported in chapter 4. The layered films exhibit epitaxial growth confirmed by both XRD and TEM results. As for magnetic characterization, mainly three results are observed. First of all, existence of BiFeO₃ film can enhance perpendicular anisotropy. The single ordered CoPt film shows isotropy due to low ordering degree, and perpendicular anisotropy is enhanced with $K \sim 1.9 \times 10^6$ erg/cm³ by further depositing BiFeO₃ on the top of CoPt films. Secondly, perpendicular exchange bias effect is detected at 50 K in BiFeO₃/Pt/L₁₀ CoPt layered structures. The coercivity H_C value is 5522 Oe and loop shift H_E value is - 646 Oe. Thirdly, a magnetic field-mediated magnetic states phenomenon in perpendicular direction is observed in BiFeO₃/Pt/L₁₀ ordered CoPt structures. Two different hysteresis loops (two magnetization steps with plateau and non-plateau shapes) can be repeatedly switched by orthogonal external magnetic field. This phenomenon is induced by different responds to external field of each layer (that is Co-containing BiFeO₃, Co-deficient CoPt and L₁₀ ordered CoPt layers) in layered architecture, which is suggested by Co segregation distribution in the cross-section element mapping image.

Chapter 5 describes longitudinal exchange bias effect in Co₂FeSi/Pt/BiFeO₃ layered films. An ultra-thin Pt layer (0.5 - 2 nm) is inserted between Co₂FeSi and BiFeO₃ films. The existence of Pt layer can prevent oxidization of Co₂FeSi, confirmed by both M_S value in hysteresis loops and Auger electron spectroscopy depth profile. After field-cooling treatment, the coercivity H_C value increases compared to that of as-deposited films, indicating the exchange bias effect. The highest H_C enlargement (from 20 to 80 Oe) happens at Co₂FeSi/Pt_{0.5nm}/BiFeO₃ films. However this sample does not show loop shift (another manifestation of exchange bias effect) at room temperature. This may be due to relatively large thickness of Co₂FeSi (6 nm) explained by random-field model.

In all, interface structure and magnetic properties of BiFeO₃/TiN, BiFeO₃/L₁₀ CoPt, Co₂FeSi/Pt/CoPt layered films are studied, respectively. Epitaxial BiFeO₃ films are prepared on conductive TiN under layers at reduced temperature ~ 500 °C. Perpendicular exchange bias effect and field-mediated magnetic states phenomenon are detected in BiFeO₃/L₁₀ CoPt layered films. Longitudinal exchange bias effect is observed in Co₂FeSi/BiFeO₃ layered films.

備考 : 論文要旨は、和文 2000 字と英文 300 語を 1 部ずつ提出するか、もしくは英文 800 語を 1 部提出してください。

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